

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
-30V	19m $\Omega$ @ $V_{GS} = -10\text{V}$	-8.7A
	45m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-5.5A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

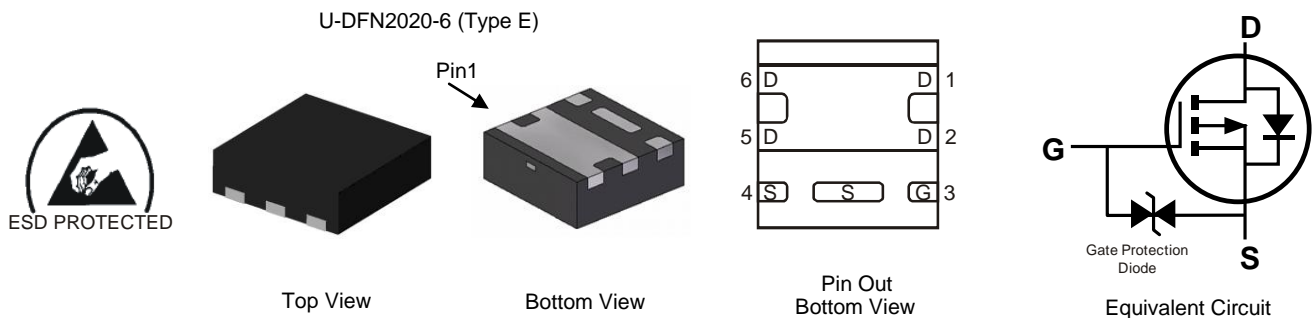
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- 0.6mm profile – ideal for low profile applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe.  
Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.007 grams (Approximate)

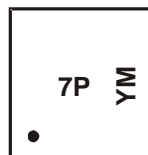


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3026SFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMP3026SFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



7P = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-8.7 -6.9	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-10.4 -8.4	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	-50	A
Continuous Source-Drain Diode Current (Note 6)		T <sub>A</sub> = +25°C	I <sub>S</sub>	-2.0	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	-23	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	27	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.72	W
	T <sub>A</sub> = +70°C		0.46	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	175	°C/W
	t < 10s		121	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.0	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	61	°C/W
	t < 10s		42	
Thermal Resistance, Junction to Case (Note 6)	Steady state	R <sub>θJC</sub>	9.3	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current T <sub>J</sub> = +150°C (Note 9)		—	—	-100		
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	15	19	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.5A
			28	45		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A
			34	54		V <sub>GS</sub> = -4.0V, I <sub>D</sub> = -3.0A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.0A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	1,204	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	154	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	112	—		
Gate Resistance	R <sub>g</sub>	—	16	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	19.6	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -9.5A
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	9.2	—		
Gate-Source Charge	Q <sub>gs</sub>	—	4.3	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	3.9	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	5.3	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -9.5A
Turn-On Rise Time	t <sub>r</sub>	—	23	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	34	—		
Turn-Off Fall Time	t <sub>f</sub>	—	26	—		
Reverse Recovery Time	t <sub>rr</sub>	—	10	—	ns	I <sub>F</sub> = -9.5A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	3.3	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = 25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

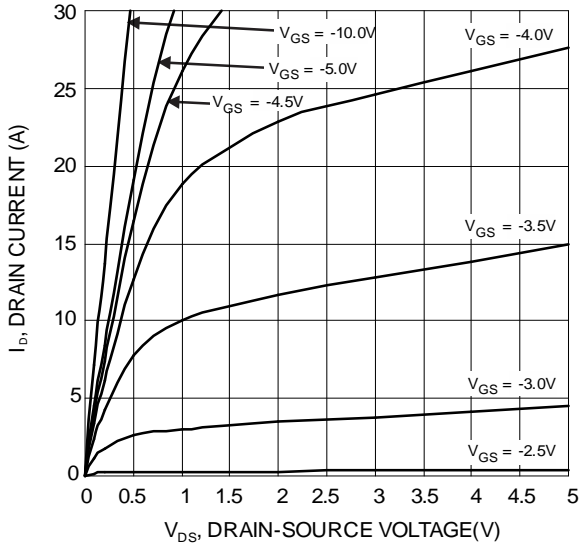


Figure 1 Typical Output Characteristic

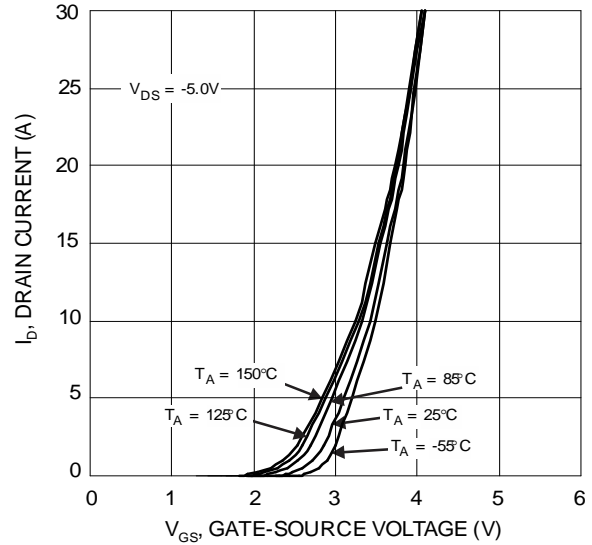


Figure 2 Typical Transfer Characteristic

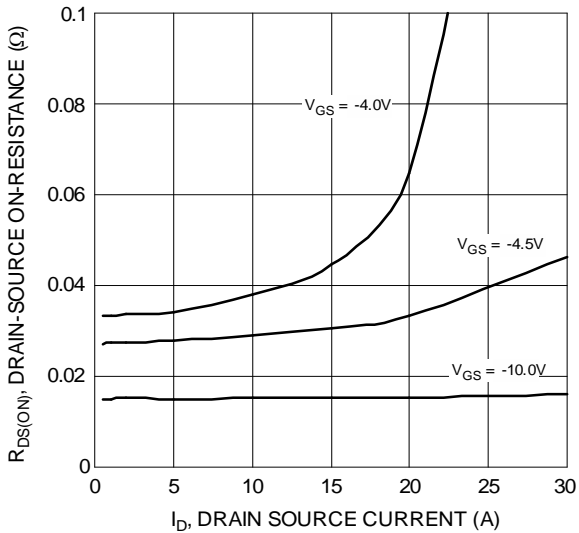


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

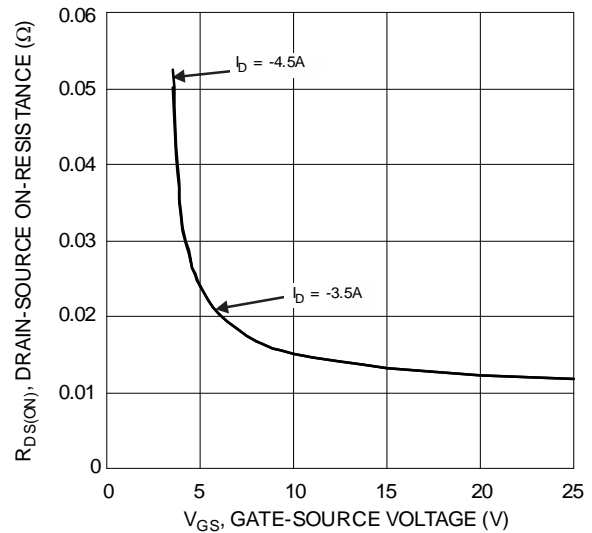


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

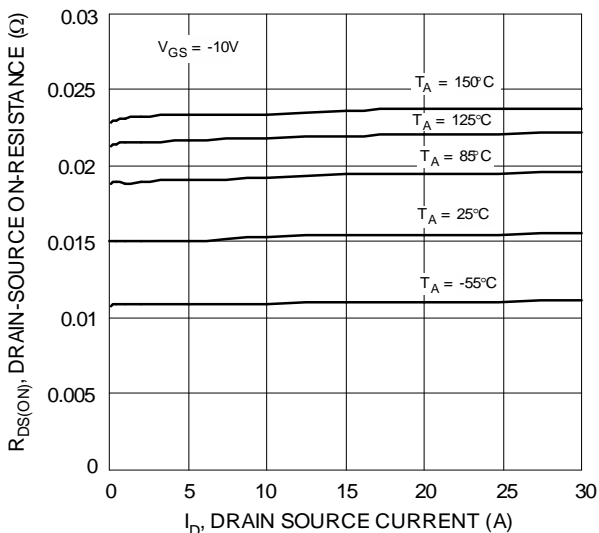


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

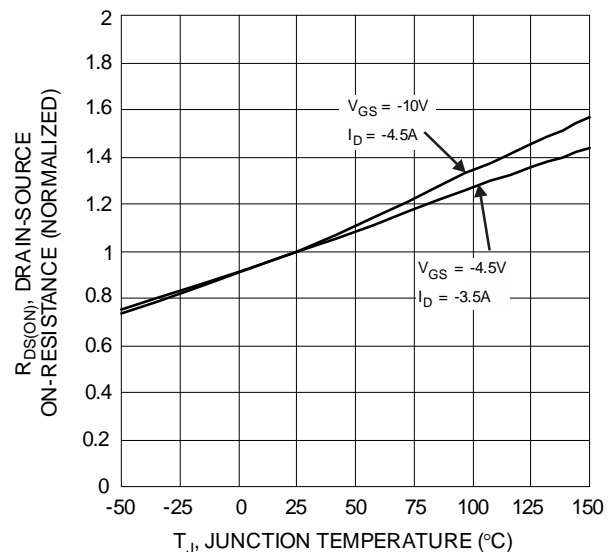


Figure 6 On-Resistance Variation with Temperature

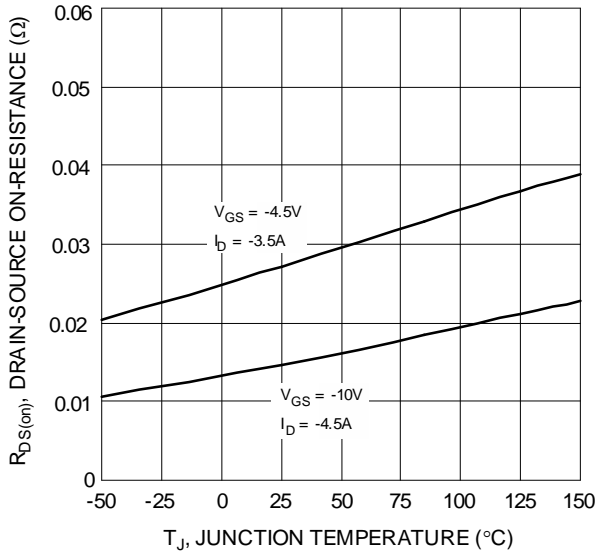


Figure 7 On-Resistance Variation with Temperature

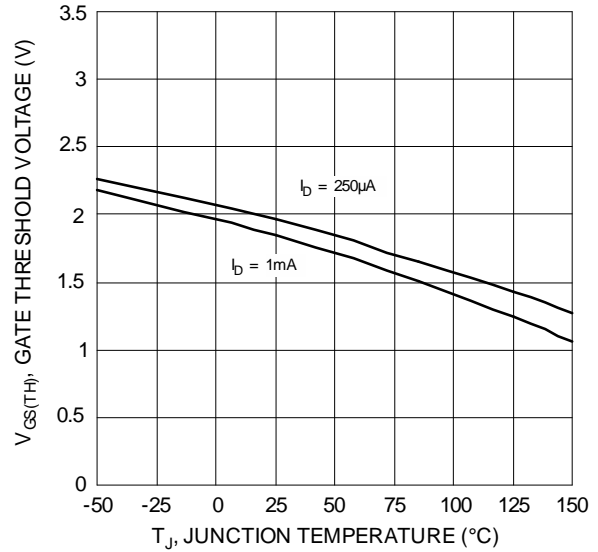


Figure 8 Gate Threshold Variation vs. Junction Temperature

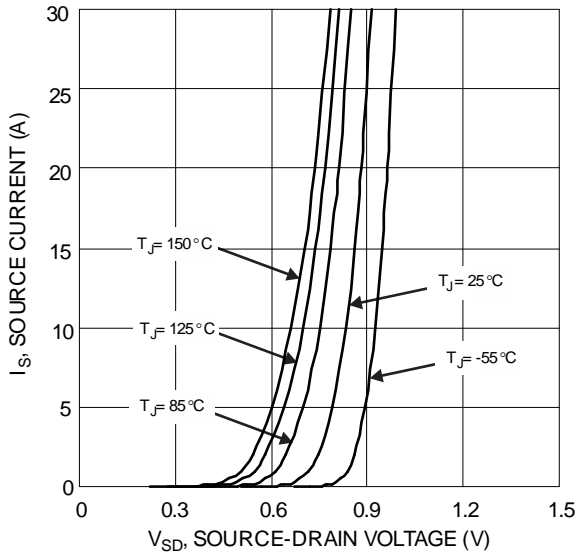


Figure 9 Diode Forward Voltage vs. Current

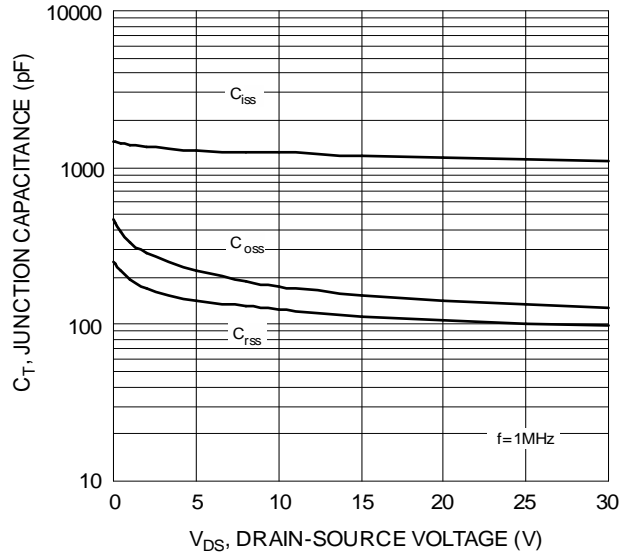


Figure 10 Typical Junction Capacitance

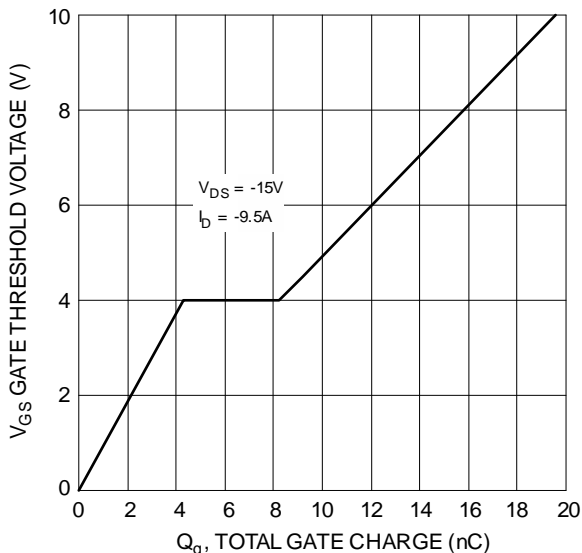


Figure 11 Gate Charge

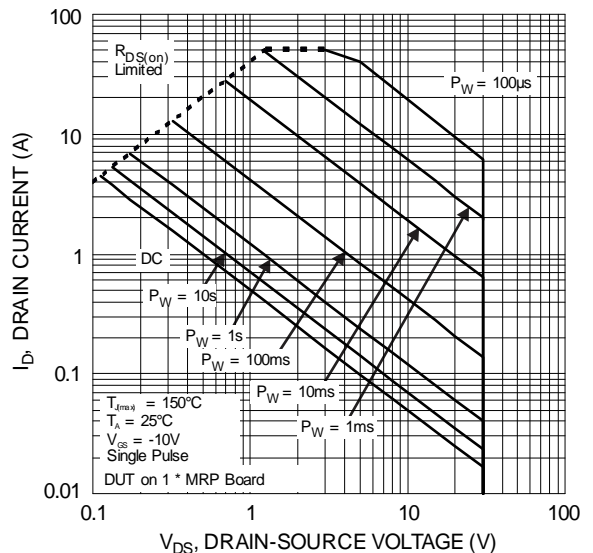


Figure 12 SOA, Safe Operation Area

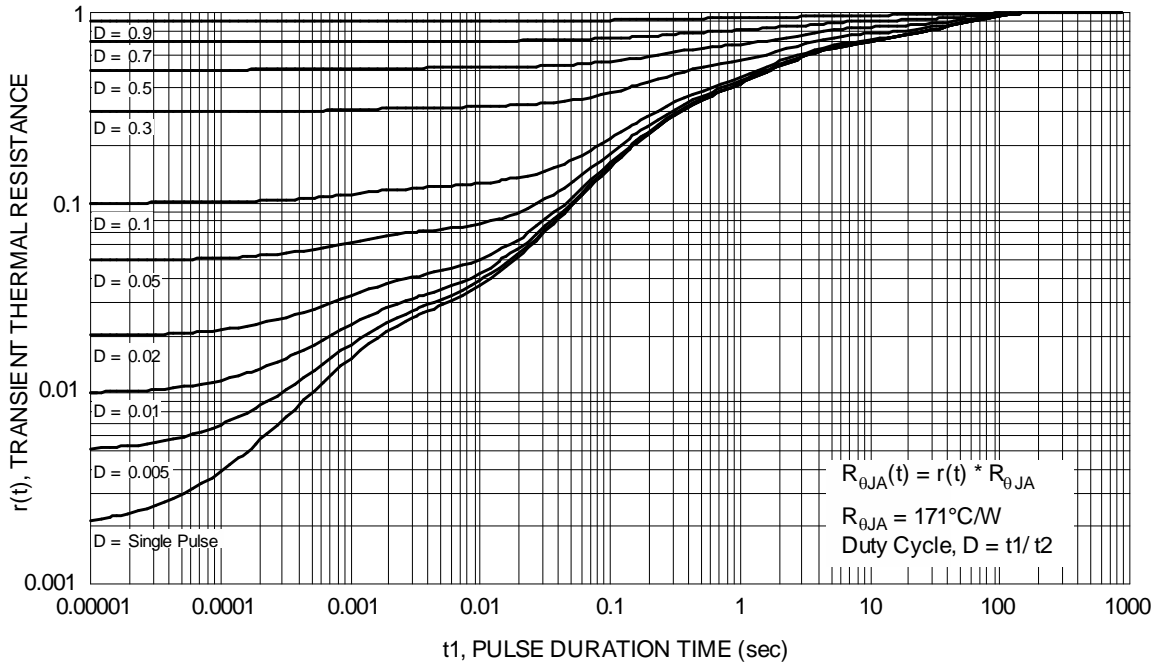
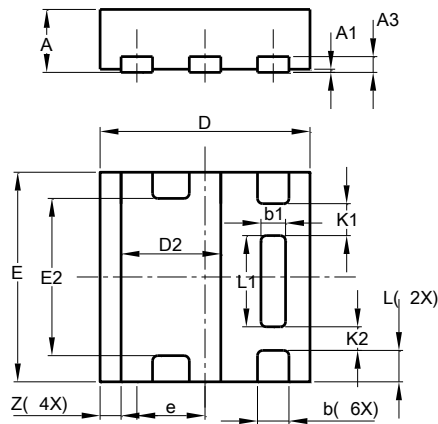


Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type E)**



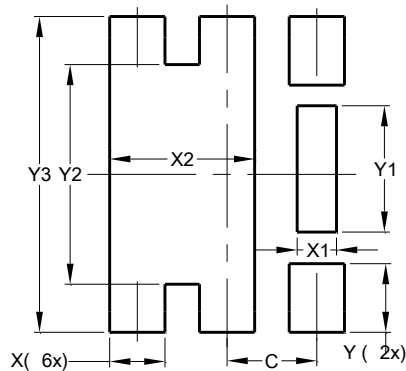
U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	-	-	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	-	-	0.305
K2	-	-	0.225
Z	-	-	0.20

**All Dimensions in mm**

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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